3. A group III nitride wafer according to claim 1, wherein the mechanical process is grinding of the wafer.

4. A group III nitride wafer according to claim 2, wherein the wafer was sliced from a bulk crystal of group III nitride with a multiple wire saw.

5. A group III nitride wafer according to claim 1, wherein the chemical treatment is etching.

6. A group III nitride wafer according to claim 5, wherein the etching is performed using a wet etchant.

7. A group III nitride wafer according to claim 6, wherein the wet etchant comprises phosphoric acid.

8. A group III nitride wafer according to claim 7, wherein the chemical treatment is etching in phosphoric acid or its mixture at 50° C. or higher.

9. A group III nitride wafer according to claim 1, wherein the wafer has c-plane orientation with misorientation from minus 10 degree to plus 10 degree.

10. A group III nitride wafer according to claim 1, wherein the wafer has a semipolar plane orientation with misorientation from minus 10 degree to plus 10 degree.

11. A group III nitride wafer according to claim 1, wherein the wafer has a nonpolar plane orientation with misorientation from minus 10 degree to minus 0.1 degree or plus 0.1 degree to plus 10 degree.

12. A group III nitride wafer according to claim 1, wherein the wafer has a surface area greater than 100 $mm^2$.

13. A group III nitride wafer according to claim 1, wherein the composition comprises GaN.

14. A group III nitride wafer comprising a first layer and a second layer of damaged group III nitride on opposite faces of a third layer of highly oriented poly or single crystalline group III nitride, wherein the first and the second layer were formed through a mechanical process that precedes chemically-mechanically polishing the wafer, and the surface of the second layer is made visually distinguishable, without instrumentation, from the surface of the first layer by a chemical etching.

15. A group III nitride wafer according to claim 14, wherein the wafer is sliced from a bulk crystal of group III nitride.

16. A group III nitride wafer according to claim 14, wherein the wafer is sliced from a bulk crystal of group III nitride with a multiple wire saw.

17. A group III nitride wafer according to claim 14, wherein the chemical etching uses acid or base.

18. A group III nitride wafer according to claim 17, wherein the chemical etching uses phosphoric acid or its mixture.

19. A group III nitride wafer according to claim 18, wherein the chemical etching uses phosphoric acid or its mixture at 50° C. or higher.

20. A group III nitride wafer according to claim 14, wherein the surface area of the wafer is more than 100 $mm^2$.

21. A group III nitride wafer according to claim 14, wherein the third layer has a density of line defect and grain boundary less than $10^6$ $cm^{-2}$.

22. A group III nitride wafer according to claim 14, wherein the group III nitride comprises GaN.

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